WHAT IS CLAIMED IS:

1. A dielectric device comprising:

such a first electrode layer that constituent elements located on its surface are terminated by halogen atoms; and

a dielectric film formed on the surface of said first electrode layer terminated by said halogen atoms.

2. The dielectric device according to claim 1, wherein

said first electrode layer contains at least one element selected from a group consisting of Pt, Ir, Pd and Ru.

3. The dielectric device according to claim 1, wherein

said halogen atoms are fluorine atoms.

4. The dielectric device according to claim 3, wherein

said first electrode layer contains Pt, and

platinum fluoride is formed on the surface of said first electrode layer.

5. The dielectric device according to claim 1, wherein

said dielectric film includes a ferroelectric film having a bismuth layer structure.

6. The dielectric device according to claim 5, wherein

said ferroelectric film having a bismuth layer structure is an $SrBi_2Ta_2O_9$ (SBT) film.

7. The dielectric device according to claim 5, wherein

a bismuth layer is formed to be substantially perpendicular to said first electrode layer in said ferroelectric film having a bismuth layer structure.

8. The dielectric device according to claim 1, further comprising a second electrode layer formed on said dielectric film.

9. The dielectric device according to claim 1, further comprising an adherent layer formed under said first electrode layer.

10. The dielectric device according to claim 9,

wherein

said adherent layer includes an IrSiN film.

11. A method of manufacturing a dielectric device comprising steps of:

terminating constituent elements located on the surface of a first electrode layer by halogen atoms; and

forming a dielectric film on the surface of said first electrode layer terminated by said halogen atoms.

12. The method of manufacturing a dielectric device according to claim 11, wherein

said step of terminating said constituent elements by said halogen atoms includes a step of exposing the surface of said first electrode layer into either a plasma or a solution containing halogen ions thereby terminating said constituent elements located on the surface of said first electrode layer by said halogen atoms.

13. The method of manufacturing a dielectric device according to claim 11, further comprising a step of performing heat treatment after formation of said dielectric film thereby crystallizing said dielectric film.

14. The method of manufacturing a dielectric device

according to claim 11, wherein

said halogen atoms are fluorine atoms.

15. The method of manufacturing a dielectric device according to claim 14, wherein

said first electrode layer contains Pt, and

platinum fluoride is formed on the surface of said first electrode layer.

16. The method of manufacturing a dielectric device according to claim 11, wherein

said step of forming said dielectric film includes a step of forming a ferroelectric film having a bismuth layer structure.

17. The method of manufacturing a dielectric device according to claim 16, wherein

said ferroelectric film having a bismuth layer structure is an $SrBi_2Ta_2O_9$ (SBT) film.

18. The method of manufacturing a dielectric device according to claim 16, wherein

said step of forming said ferroelectric film having a bismuth layer structure includes a step of forming said ferroelectric film having a bismuth layer structure so

that a bismuth layer is substantially perpendicular to said first electrode layer.

19. The method of manufacturing a dielectric device according to claim 11, further comprising a step of forming a second electrode layer on said dielectric film.

20. The method of manufacturing a dielectric device according to claim 11, further comprising a step of forming an adherent layer under said first electrode layer.

21. The method of manufacturing a dielectric device according to claim 20, wherein

said adherent layer includes an IrSiN film.